

**IN THE CLAIMS:**

Claims 1-15 (canceled)

16. (currently amended) A semiconductor device having a semiconductor chip,  
first electrodes formed on said semiconductor chip,  
barrier metals formed on said first electrodes and having laminated structures, and  
a plurality of second protruded electrodes, which serve as external connection terminals, formed  
on said barrier metals, wherein said barrier metals comprising:  
a lowermost conductive metal layer laminated on said first electrodes, said lowermost  
conductive metal layer being made of a metal selected from the group consisting of titanium (Ti), chromium  
(Cr) and molybdenum (Mo) and having a joining property with said first electrodes;  
an intermediate conductive metal layer laminated on said lowermost conductive metal layer,  
said intermediate conductive metal layer being made of nickel (Ni); and  
an uppermost conductive metal layer laminated on said intermediate conductive metal layer,  
said uppermost conductive metal layer being made of a material which easily alloys with the nickel of said  
intermediate conductive metal layer and which has resistance to oxidation, said uppermost conductive metal  
layer being made of a metal selected from the group consisting of platinum (Pt), palladium (Pd), silver (Ag)  
and rhodium (Rh) or of an alloy containing a metal selected from the group consisting of gold (Au), platinum  
(Pt), palladium (Pd), silver (Ag) and rhodium (Rh).

17. (previously amended) A semiconductor device as claimed in claim 16, wherein the weight of said uppermost conductive metal layer is less than 2 weight % of the weight of the bump to be formed thereon.